

# **Product Specification**

# XBLW LMV321A, LMV358A, LMV324A

1MHz, General Purpose, RRIO CMOS Amplifiers







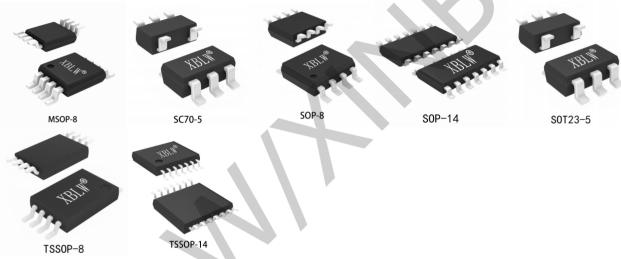


### **Descriptions**

The XBLW LMV321A (single), XBLW LMV358A (dual) and XBLW LMV324A (quad) are general purpose, low offset, high frequency response and micro power operational amplifiers. With an excellent bandwidth of 1MHz, a slew rate of  $0.8V/\mu$ s, and a quiescent current of  $80\mu$ A per amplifier at 5V, the XBLW LMV321A/358A/324A family can be designed into a wide range of applications.

The XBLW LMV321A/358A/324A op-amps are designed to provide optimal performance in low voltage and low power systems. The input common-mode voltage range includes ground, and the maximum input offset voltage are 4.5 mV. These parts provide rail-to-rail output swing into heavy loads. The XBLW LMV321A/358A/324A family is specified for single or dual power supplies of +2.3V to +5.5V. All models are specified over the extended industrial temperature range of +40°C to +125°C.

The XBLW LMV321A is available in 5-lead SOT-23 and SC70-5 package. The XBLW LMV358A is available in 8-lead SOP package. The XBLW LMV324A is available in 14-lead SOP package.



#### **Feature**

- General Purpose 1MHz Amplifiers, Low Cost
- > High Slew Rate: 0.8V/μs
- ➤ Low Offset Voltage: 4.5 mV Maximum
- Low Power: 80μA per Amplifier Supply Current
- Settling Time to 0.1% with 2V Step: 4.2 μs
- Unit Gain Stable
- ➤ Rail-to-Rail Input and Output
- ➤ Input Voltage Range: -0.1V to +5.1V at 5V Supply
- ➤ Operating Power Supply: +2.3V to +5.5V
- $\triangleright$  Operating Temperature Range: -40°C to +125°C
- ➤ ESD Rating: HBM-4kV, CDM-2kV
- Upgrade to LMV321A/LMV358A/LMV324A Family

## **Applications**

- Active Filter
- Smoke/Gas/Environment Sensors
- Audio Outputs
- Battery and Power Supply Control
- > Portable Equipment and Mobile Devices
- Active Filters
- Sensor Interfaces
- Battery-Powered Instrumentation
- Medical Instrumentation

### **Ordering Information**

DEVICE	Dackage Type	MADIZING	Doolsing	Docking OTV
DEAICE	Package Type	MARKING	Packing	Packing QTY
LMV321ATDTR	SOT23-5	V321A	Tape	3000/Reel
LMV321ACDTR	SC70-5	V321A	Tape	3000/Reel
LMV358ADTR	SOP-8	LMV358A	Tape	2500/Reel
LMV358AMDTR	MSOP-8	V358AM	Tape	3000/Reel
LMV358ATDTR	TSSOP-8	V358AT	Tape	3000/Reel
LMV324ADTR	SOP-14	LMV324A	Tape	2500/Reel
LMV324ATDTR	TSSOP-14	V324AT	Tape	2500/Reel



## **Pin Configurations**

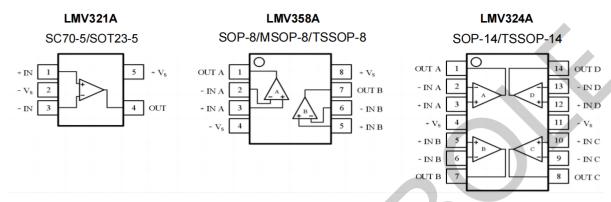


Figure 1 Pin Configurations

### **Pin Description**

Symbol	Description
-IN	Negative (inverting) input.
+IN	Positive (noninverting) input.
-INA, -INB -INC, -	Inverting Input of the Amplifier. The Voltage range can go from $(V_{S-} - 0.1V)$ to $(V_{S+} + 0.1V)$
IND	1V).
+INA, +INB +INC, +IND	Non-Inverting Input of Amplifier. This pin has the same voltage range as -IN.
+V <sub>S</sub>	Positive Power Supply. The voltage is from 2.3V to 5.5V. Split supplies are possible as long as the voltage between V <sub>S+</sub> and V <sub>S-</sub> is between 2.3V and 5.5V. A bypass capacitor of 0.1 µF as close to the part as possible should be used between power supply pins or between supply pins and ground
	Negative Power Supply. It is normally tied to ground. It can also be tied to a
	voltage other than ground as long as the voltage between $V_{S^+}$ and $V_{S^-}$ is from
-Vs	2.3V to 5.5V. If it is not connected to ground, bypass it with a capacitor of 0.
	1μF as close to the part as possible.
OUT	Output.
OUTA, OUTB OUTC, OUTD	Amplifier Output

# **Absolute Maximum Ratings (TA= 25°C)**

Symbol	Description	Value	Units
V <sub>S+</sub> ,V <sub>S-</sub>	Supply Voltage, V <sub>S+</sub> to V <sub>S-</sub>	7.0	V
VcM	Common-Mode Input Voltage	$V_{S^-} - 0.3$ to $V_{S^+} + 0.3$	V
		HBM ±4000	V
ESD	Electrostatic Discharge Voltage	CDM ±2000	V
TJ	Junction Temperature	160	°C
Tstg	Storage Temperature Range	-65 to +150	°C(T <sub>J</sub> )
TJL	Lead Temperature Range (Soldering 10 sec)	260	°C

#### Notes:

<sup>1.</sup> Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

<sup>2.</sup> Provided device does not exceed maximum junction temperature (TJ) at any time.

### **Electrical Characteristics**

 $V_S$  = 5.0V,  $T_A$  = +25°C,  $V_{CM}$  =  $V_S/2$ ,  $V_O$  =  $V_S/2$ , and  $R_L$  = 10k $\Omega$  connected to  $V_S/2$ , unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
INPUT CHA	ARACTERISTICS					
	Input offset voltage		-4.5	±1.0	+4.5	
Vos	Over temperature		-4.8		+4.8	mV
Vos TC	Offset voltage drift	Over Temperature		2.3		μV/°C
	Input bias current			1		
lΒ	Over temperature		<b>9</b> 5	500		рА
los	Input offset current			1		рА
Vсм	n-mode voltage range		Vs0.1		V <sub>S+</sub> +0.1	V
	n-mode rejection ratio			90		
	Over temperature	$V_{CM} = 0.05V \text{ to } 3.5V$		85		
CMRR				80		dB
	Over temperature	$V_{CM} = V_{S-} - 0.1$ to $V_{S+} + 0.1$ V		75		
	Open-loop voltage gain			110		
Avol	Over temperature	$V_0 = 0.05 \text{ to } 3.5 \text{ V}$		100		dB
Rin	Input resistance	7	100			GΩ
		Differential		2.0		
CIN	Input capacitance	Common mode		3.5		pF
OUTPUT C	HARACTERISTICS					
Vон	High output voltage swing			V <sub>S+</sub> -8		mV
Vol	Low output voltage swing			8		mV
	Closed-loop output impedance	f= 200kHz, G = +1		0.4		
Zоuт	Open-loop output impedance	f= 1MHz, l <sub>0</sub> = 0		2.6		Ω
,		Source current through 10Ω		40		
Isc	Short-circuit current	Sink current through 10Ω		40		mA
DYNAMIC I	PERFORMANCE					
GBW	Gain bandwidth product	f= 1kHz		1.0		MHz
Фм	Phase margin	C <sub>L</sub> = 100pF		62		0
SR	Slew rate	G = +1, $C_L$ = 100pF, $V_O$ = 1.5V to 3.5V		0.8		V/µs



### **Electrical Characteristics**

 $V_S = 5.0 V$ ,  $T_A = +25 \,^{\circ}\text{C}$ ,  $V_{CM} = V_S/2$ ,  $V_O = V_S/2$ , and  $R_L = 10 \mathrm{k}\Omega$  connected to  $V_S/2$ , unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
		To 0.1%, G = +1, 2V step		4.2		
<b>t</b> s	Settling time To 0.01%, G = +1, 2V step			5.2		μs
<b>t</b> or	Overload recovery time	V <sub>IN</sub> * Gain > V <sub>S</sub>		2		μs
THD+N	Total harmonic distortion+Noise	f= 1kHz, G = +1, V <sub>O=</sub> 3V <sub>PP</sub>	V	0.003		%
		NOISE PERFORMANCE				
Vn	Input voltage noise	f = 0.1 to 10 Hz		13		$\mu V_{P-P}$
<b>e</b> n	Input voltage noise density	f= 1kHz		35		nV/√Hz
In	Input current noise density	f= 10kHz		6		fA/√Hz
		POWER SUPPLY				
Vs	Operating supply voltage		2.3		5.5	V
	Power supply rejection ratio	$V_{\rm S}$ = 2.7V to 5.5V, $V_{\rm CM} < V_{\rm S+}$ -		98		
PSRR	Over temperature	2V		85		dB
	Quiescent current (per amplifier)			80	120	
la 🚺	Over temperature			85	130	μA
		THERMAL CHARACTERISTIC	S	-		
TA	Operating temperature range		-40		+125	°C
		SOT23-5		190		
$oldsymbol{ heta}_{\sf JA}$	Package thermal resistance	SO-8		125		°C/W
-5/1		SO-14		115		

Specifications subject to changes without notice



### **Typical Performance Characteristics**

At  $T_A$  = +25°C,  $V_{CM}$  =  $V_S/2$ , and  $R_L$  = 10k $\Omega$  connected to  $V_S/2$ , unless otherwise noted.

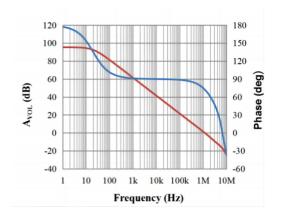
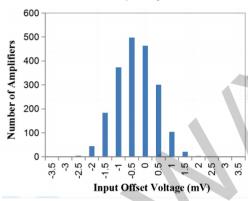


Figure 2 Open-loop Gain and Phase as function of Frequency



120
100
80
80
40
PSRR

0
-20
1 10 100 1k 10k 100k 1M 10M
Frequency (Hz)

Figure 3 Power Supply and Common-mode RejectionRatio a as a function of Frequency

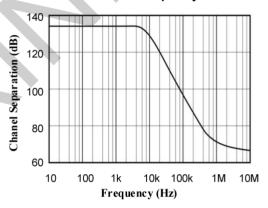


Figure 4 Input Offset Voltage Production DistributionFigure 5 Channel Separation as a function of Frequency

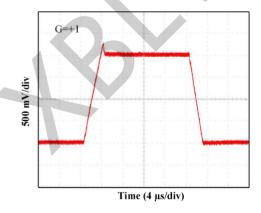
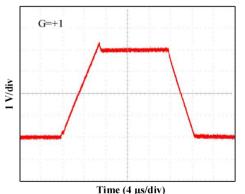


Figure 6 Large-Signal Step Response at 2.7V



Time (4 μs/div)
Figure 8 Large-Signal Step Response at 5V

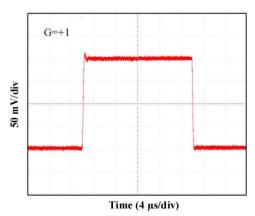


Figure 7 Small-Signal Step Response at 2.7V

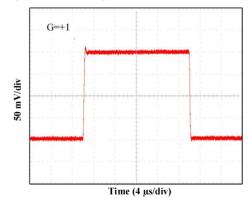


Figure 9 Small-Signal Step Response at 5V

### **Application Notes**

#### 1. LOW INPUT BIAS CURRENT

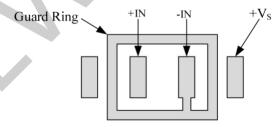
The XBLW LMV321A/358A/324A family is a CMOS op-amp family and features very low input bias current in pA range. The low input bias current allows the amplifiers to be used in applications with high resistance sources. Care must be taken to minimize PCB Surface Leakage. See below section on "PCB Surface Leakage" for more details.

#### 2. PCB SURFACE LEAKAGE

In applications where low input bias current is critical, Printed Circuit Board (PCB) surface leakage effects need to be considered. Surface leakage is caused by humidity, dust or other contamination on the board. Under low humidity conditions, a typical resistance between nearby traces is  $1012\Omega$ . A 5V difference would cause 5pA of current to flow, which is greater than the XBLW LMV321A/358A/324A's input bias current at  $\pm 25^{\circ}$ C ( $\pm 1f$ A, typical). It is recommended to use multi-layer PCB layout and route the op-amp's -IN and +IN signal under the PCB surface.

The effective way to reduce surface leakage is to use a guard ring around sensitive pins (or traces). The guard ring is biased at the same voltage as the sensitive pin. An example of this type of layout is shown in Figure 10 for Inverting Gain application.

- 1. For Non-Inverting Gain and Unity-Gain Buffer:
- a) Connect the non-inverting pin (+IN) to the input with a wire that does not touch the PCB surface.
- b) Connect the guard ring to the inverting input pin (-IN). This biases the guard ring to the Common Mode input voltage.
  - 2. For Inverting Gain and Trans-impedance Gain Amplifiers (convert current to voltage, such as photo detectors):
- a) Connect the guard ring to the non-inverting input pin (+IN). This biases the guard ring to the same reference voltage as the op-amp  $(e.g., V_s/2 \text{ or ground})$ .
  - b) Connect the inverting pin (-IN) to the input with a wire that does not touch the PCB surface.



#### 3. GROUND SENSING AND RAIL TO RAIL

The input common-mode voltage range of the XBLW LMV321A/358A/324A series extends  $100\,\text{mV}$  beyond the supply rails. This is achieved with a complementary input stage—an N- channel input differential pair in parallel with a P-channel differential pair. For normal operation, inputs should be limited to this range. The absolute maximum input voltage is  $300\,\text{mV}$  beyond the supplies. Inputs greater than the input common-mode range but less than the maximum input voltage, while not valid, will not cause any damage to the op-amp. Unlike some other op-amps, if input current is limited, the inputs may go beyond the supplies without phase inversion, as shown in Figure 11. Since the input common-mode range extends from  $(V_{S^+}-0.1V)$  to  $(V_{S^+}+0.1V)$ , the XBLW LMV321A/358A/324A opamps can easily perform 'true ground' sensing.

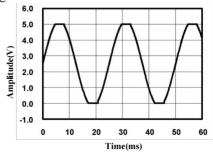


Figure 11 No Phase Inversion with Inputs Greater Than the Power-Supply Voltage



1MHz, General Purpose, RRIO CMOS Amplifiers

A topology of class AB output stage with common-source transistors is used to achieve ail-to-rail output. For light resistive loads (e.g.  $100k\Omega$ ), the output voltage can typically swing to within 5mV from the supply rails. With moderate resistive loads (e.g.  $10k\Omega$ ), the output can typically swing to within 10mV from the supply rails and maintain high open-loop gain.

The maximum output current is a function of total supply voltage. As the supply voltage to the amplifier increases, the output current capability also increases. Attention must be paid to keep the junction temperature of the IC below 150°C when the output is in continuous short-circuit. The output of the amplifier has reverse-biased ESD diodes connected to each supply. The output should not be forced more than 0.5V beyond either supply, otherwise current will flow through these diodes.

#### 4. CAPACITIVE LOAD AND STABILITY

The XBLW LMV321A/358A/324A can directly drive 1nF in unity-gain without oscillation. The unity-gain follower (buffer) is the most sensitive configuration to capacitive loading. Direct capacitive loading reduces the phase margin of amplifiers and this results in ringing or even oscillation. Applications that require greater capacitive drive capability should use an isolation resistor between the output and the capacitive load like the circuit in Figure 12. The isolation resistor RISO and the load capacitor CL form a zero to increase stability. The bigger the RISO resistor value, the more stable VOUT will be. Note that this method results in a loss of gain accuracy because RISO forms a voltage divider with the RL.

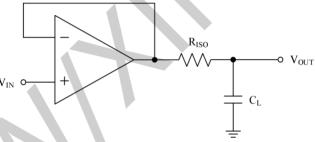


Figure 12 Indirectly Driving Heavy Capacitive Load

An improvement circuit is shown in Figure 13. It provides DC accuracy as well as AC stability. The  $R_F$  provides the DC accuracy by connecting the inverting signal with the output. The  $C_F$  and  $R_{ISO}$  serve to counteract the loss of phase margin by feeding the high frequency component of the output signal back to the amplifier's inverting input, thereby preserving phase margin in the overall feedback loop.

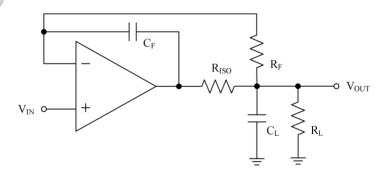


Figure 13 Indirectly Driving Heavy Capacitive Load with DC Accuracy

For no-buffer configuration, there are two others ways to increase the phase margin: (a) by increasing the amplifier's gain, or (b) by placing a capacitor in parallel with the feedback resistor to counteract the parasitic capacitance associated with inverting node.

XBLW Version2.0 8/18 www.xinboleic.com

1MHz, General Purpose, RRIO CMOS Amplifiers

#### 5. POWER SUPPLY LAYOUT AND BYPASS

The XBLW LMV321A/358A/324A family operates from either a single  $+2.3\,V$  to  $+5.5\,V$  supply or dual  $\pm1.15\,V$  to  $\pm2.75\,V$  supplies. For single-supply operation, bypass the power supply Vs with a ceramic capacitor (i.e.  $0.01\,\mu\text{F}$  to  $0.1\,\mu\text{F}$ ) which should be placed close (within 2mm for good high frequency performance) to the Vs pin. For dual-supply operation, both the Vs+ and the Vs- supplies should be bypassed to ground with separate  $0.1\,\mu\text{F}$  ceramic capacitors. A bulk capacitor (i.e.  $2.2\,\mu\text{F}$  or larger tantalum capacitor) within  $100\,\text{mm}$  to provide large, slow currents and better performance. This bulk capacitor can be shared with other analog parts.

Good PC board layout techniques optimize performance by decreasing the amount of stray capacitance at the op - amp's inputs and output. To decrease stray capacitance, minimize trace lengths and widths by placing external components as close to the device as possible. Use surface-mount components whenever possible. For the op-amp, soldering the part to the board directly is strongly recommended. Try to keep the high frequency big current loop area small to minimize the EMI (electromagnetic interfacing).

#### 6. GROUNDING

A ground plane layer is important for the XBLW LMV321A/358A/324A circuit design. The length of the current path speed currents in an inductive ground return will create an unwanted voltage noise. Broad ground plane areas will reduce the parasitic inductance.

#### 7. INPUT-TO-OUTPUT COUPLING

To minimize capacitive coupling, the input and output signal traces should not be parallel. This helps reduce unwanted positive feedback.

### **Typical Application Circuits**

#### 1. DIFFERENTIAL AMPLIFIER

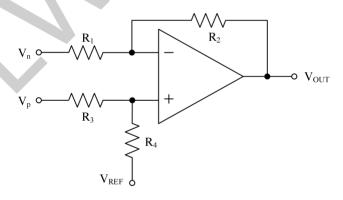
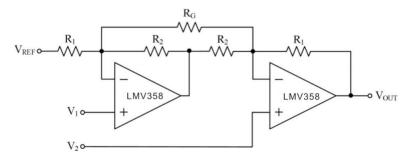


Figure 14 Differential Amplifier

The circuit shown in Figure 14 performs the difference function. If the resistors ratios are equal  $R_4/R_3 = R_2/R_1$ , then:  $V_{OUT} = (V_p - V_n) \times R_2/R_1 + V_{REF}$ 

#### 2. INSTRUMENTATION AMPLIFIER



 $V_{OUT} = (V_1 - V_2) \times (1 + R_1/R_2 + 2R_1/R_G) + V_{REF}$ Figure 15 Instrumentation Amplifier

1MHz, General Purpose, RRIO CMOS Amplifiers

The XBLW LMV321A/358A/324A family is well suited for conditioning sensor signals in battery-powered applications. Figure 15 shows a two op-amp instrumentation amplifier, using the XBLW LMV358A op-amps. The circuit works well for applications requiring rejection of common-mode noise at higher gains. The reference voltage ( $V_{REF}$ ) is supplied by a low- impedance source. In single voltage supply applications, the  $V_{REF}$  is typically  $V_{S}/2$ .

#### 3. BUFFERED CHEMICAL SENSORS

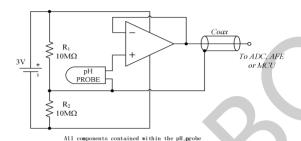
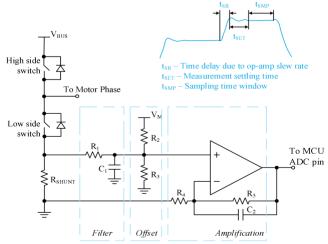


Figure 16 Buffered pH Probe

The XBLW LMV321A/358A/324A family has input bias current in the pA range. This is ideal in buffering high impedance chemical sensors, such as pH probes. As an example, the circuit in Figure 16 eliminates expansive low-leakage cables that is required to connect a pH probe (general purpose combination pH probes, e.g Corning 476540) to metering ICs such as ADC, AFE and/or MCU. An XBLW LMV321A/358A/324A op-amp and a lithium battery are housed in the probe assembly. A conventionallow-cost coaxial cable can be used to carry the op-amp's output signal to subsequent ICs for pH reading.

#### 4. SHUNT-BASED CURRENT SENSING AMPLIFIER

The current sensing amplification shown in Figure 8 has a slew rate of  $2\pi fVPP$  for the output of sine wave signal, and has a slew rate of 2fVPP for the output of triangular wave signal. In most of motor control systems, the PWM frequency is at 10kHz to 20kHz, and one cycle time is  $100\mu s$  for a 10kHz of PWM frequency. In current shunt monitoring for a motor phase, the phase current is converted to a phase voltage signal for ADC sampling. This sampling voltage signal must be settled before entering the ADC. As the Figure 19 shown, the total settling time of a current shunt monitor circuit includes: the rising edge delay time (tSR) due to the op-amp's slew rate, and the measurement settling time (tSET). For a 3-shunt solution in motor phase current sensing, if the smaller duty cycle of the PWM is defined at 45% (In fact, the phase with minimum PWM duty cycle, such as 5%, is not detected current directly, and it can be calculated from the other two phase currents), and the tSR is required at 20% of a total time window for a phase current monitoring, in case of a 3.3 V motor control system(3.3 V MCU with 12-bit ADC), the op-amp's slew rate should be more than:



 $3.3V / (100\mu s \times 45\% \times 20\%) = 0.37 V/\mu s$ 

At the same time, the op-amp's bandwidth should be much greater than the PWM frequency, like 10 time at least.



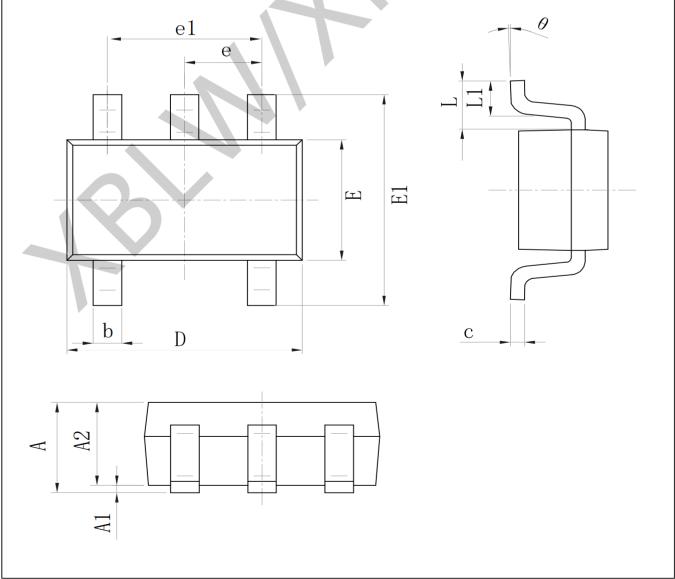
# **Package Information**

• SOT23-5

SIZE	Dimensions In	Millimeters	SIZE	Dimensions 1	In Inches
SYMBOL	MIN (mm)	MAX (mm)	SYMBOL	MIN(in)	MAX(in)
A	1.050	1.250	A	0.041	0.049
A1	0.000	0.100	A1	0.000	0.004
A2	1.050	1.150	A2	0.041	0.045
b	0.300	0.500	b	0.012	0.020
С	0.100	0.200	С	0.004	0.008
D	2.820	3.020	D	0.111	0.119
Е	1.500	1. 700	Е	0.059	0.067
E1	2.650	2. 950	E1	0. 104	0.116
е		5 (BSC)	e		87 (BSC)
e1	1.800	2.000	e1	0.071	0.079
L	0.300	0.600	L	0.012	0.024
θ	0°	8°	θ	0°	8°
田		e e1		C	

# • SC70-5

Size	Dimensions In	Millimeters	Size	Dimensions	In Inches
Symbol	Min(mm)	Max(mm)	Symbol	Min(in)	Max(in)
A	0.800	1. 100	A	0.035	0.043
A1	0.000	0.100	A1	0.000	0.004
A2	0.800	0.900	A2	0.035	0.039
b	0.150	0.350	b	0.006	0.014
С	0.080	0.150	С	0.003	0.006
D	1.850	2. 150	D	0.079	0.087
Е	1.100	1.400	Е	0.045	0.053
E1	1.950	2. 200	E1	0.085	0.096
е	0.8	5(typ)	e	0.026(typ)	
e1	1.200	1.400	e1	0.047	0.055
L	0.42(ref)		L	0.0	21 (ref)
L1	0.260	0.460	L1	0.010	0.018
θ	0°	8°	θ	0°	8°





# • SOP-8

					A
Size	Dimensions In	Millimeters	Size	Dimensions	In Inches
Symbol	Min(mm)	Max (mm)	Symbol	Min(in)	Max(in)
A	1. 350	1. 750	A	0. 053	0, 069
A1	0. 100	0. 250	A1	0.004	0. 010
A1		1. 550	A1		
A2	1. 350	1. 550	A2	0.053	0.061
b	0.330	0. 510	b	0.013	0. 020
С	0.170	0.250	С	0.006	0. 010
D	4.700	5. 100	D	0. 185	0. 200
E	3.800	4.000	E	0. 150	0. 157
E1	5. 800	6. 200	E1	0. 228	0. 224
е	1. 2'	70 (BSC)	е		50 (BSC)
L	0. 400	1 270	L	0.016	0.050
θ	0° 400	1. 270 8°	θ	0.010 0°	0.050 8°
U	0	δ	0	U	8
	AI A	D e		в — — — — — — — — — — — — — — — — — — —	

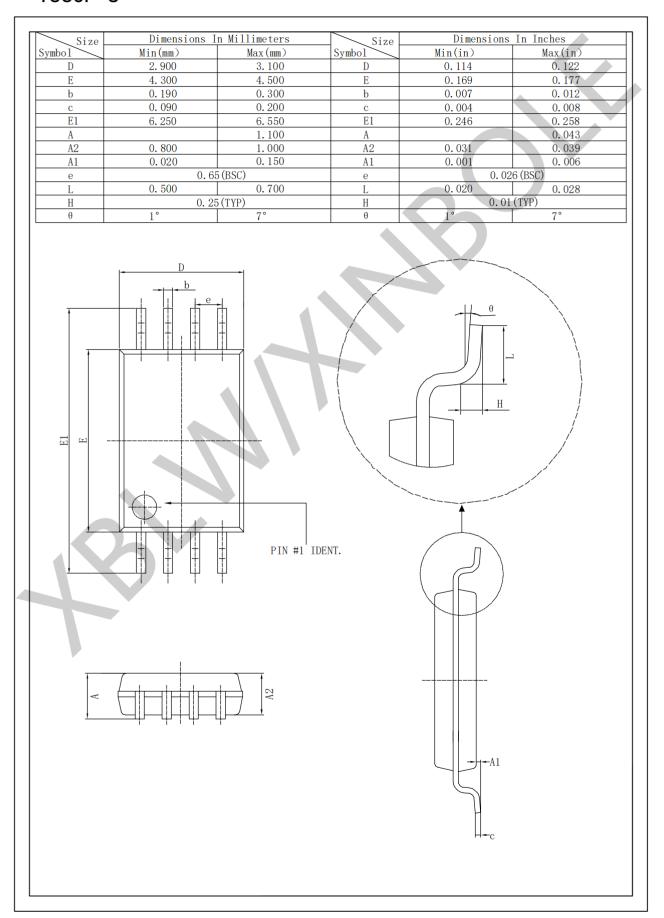


### · MSOP-8

Size	Dimensions In	n Millimeters	Size	Dimension	s In Inches
mbol	Min(mm)	Max (mm)	Symbol	Min(in)	Max(in)
A	0.820	1. 100	A	0.320	0.043
A1	0.020	0. 150	A1	0.001	0.006
A2	0.750	0. 950	A2	0.030	0. 037
b	0.250	0. 380	b	0.010	0.015
С	0.090	0. 230	c	0.004	0.009
D	2.900	3. 100	D	0.114	0.122
e		5 (BSC)		0.114	0.122 026 (BSC)
E	2.900	3. 100	e E	0.114	0. 122
E1	4. 750	5. 050	E1	0. 114	0. 122
L	0.400	0.800		0. 016	
θ	0.400 0°	6°	L 0	0.016 0°	0. 031 6°
13 E					
A A2	D D	e	<u> </u>		L



### · TSSOP-8



### · SOP-14

Size	Dimensions In		Size		In Inches
Symbol	Min(mm)	Max(mm)	Symbol	Min(in)	Max(in)
A	1. 350	1. 750	A	0.050	0.068
A1	0. 100	0. 250	A1	0.004	0.009
A2	1. 100	1. 650	A2	0.040	0.060
В	0.330	0.510	B	0. 010	0.020
С	0. 190	0. 250	C	0.007	0.009
D	8. 550	8. 750	D	0.330	0.340
Е	3. 800	4. 000	Е	0.150	0.150
е	1.		е		. 05
Н	5. 800	6. 200	Н	0. 220	0.240
h	0. 250	0.500	h	0.009	0.020
L	0.400	1. 270	L	0.015	0.050
k	8° (	max)	k	8°	(max)
E	D D	e	H AZ		h X 45°

### · TSS0P-14

Symbol   Min (mm)   Max (mm)   Symbol   Min (in)   Max (in)						
A	Size			Size		
A1		Min(mm)			Min(in)	Max(in)
A2     0.800     1.050     A2     0.031     0.041       b     0.190     0.300     b     0.007     0.012       c     0.099     0.200     c     0.004     0.0089       D     4.900     5.100     D     0.193     0.201       E     6.200     6.600     E     0.244     0.260       EI     4.300     4.500     E1     0.169     0.176       e     0.65     e     0.0256       L     0.450     0.750     L     0.018     0.030       L1     1.00     L1     0.039       k     0°     8°     k     0°     8°			1. 200			0.047
b 0.190 0.300 b 0.007 0.012   c 0.090 0.200 c 0.004 0.0089   D 4.900 5.100 D 0.193 0.201   E 6.200 6.600 E 0.244 0.266   E1 4.300 4.500 E1 0.169 0.176   e 0.65 e 0.0256   L 0.450 0.750 L 0.018 0.030   L1 1 1.00   k 0° 8° k 0° 8° k 0° 8°	Al		0.150	Al	0.002	0.006
c     0.090     0.200     c     0.004     0.089       D     4.900     5.100     D     0.193     0.201       E     6.200     6.600     E     0.244     0.260       E1     4.300     4.500     E1     0.169     0.176       e     0.65     e     0.0256       L     0.450     0.750     L     0.018     0.030       L1     1.00     B°     k     0°     8°		0.800	1.050		0.031	0.041
D 4.900 5.100 D 0.193 0.201 E 6.200 6.600 E 0.244 0.266 E1 4.300 4.500 E1 0.169 0.176 e 0.065 e 0.0256  L 0.450 0.750 L 0.018 0.030  L1 1.00 L1 0.039  k 0° 8° k 0° 8°					0.007	0.012
E 6.200 6.600 E 0.244 0.260 E1 4.300 4.500 E1 0.169 0.176 e 0.655 e 0.0256 L 0.450 0.750 L 0.018 0.030 L1 1.00 L1 0.039 k 0° 8° k 0° 8°		0.090	0. 200			0.0089
E1 4.300 4.500 E1 0.169 0.176  e 0.65 e 0.0256  L 0.450 0.750 L 0.018 0.030  L1 1.00 L1 0.039  k 0° 8° k 0° 8°		4. 900	5. 100	D	0. 193	0. 201
e 0.65 e 0.0256  L 0.450 0.750 L 0.018 0.030  L1 1.00 8° k 0° 8°		6. 200	6.600		0. 244	0. 260
L 0.450   0.750   L 0.018   0.030   L1   0.039   8°   k 0°   8°						
L1 1.00 L1 0.039 8°		0.	65			
					0.018	0.030
		1.	00	L1	0.039	
	k	0°	8°	k	0°	8°
PIN #1 IDENT.						-c
O. 25 mm GAGE PLANE  L  L  L  L  L  L  L  L  L  L  L  L  L				<del>   </del> <del> </del>	L	GAGE PLANE



1MHz, General Purpose, RRIO CMOS Amplifiers

#### Statement:

- XBLW reserves the right to modify the product manual without prior notice! Before placing an order, customers need to confirm whether the obtained information is the latest version and verify the completeness of the relevant information.
- Any semi-guide product is subject to failure or malfunction under specified conditions. It is the buyer's responsibility to comply with safety standards when using XBLW products for system design and whole machine manufacturing. And take the appropriate safety measures to avoid the potential in the risk of loss of personal injury or loss of property situation!
- XBLW products have not been licensed for life support, military, and aerospace applications, and therefore XBLW is not responsible for any consequences arising from the use of this product in these areas.
- If any or all XBLW products (including technical data, services) described or contained in this document are subject to any applicable local export control laws and regulations, they may not be exported without an export license from the relevant authorities in accordance with such laws.
- The specifications of any and all XBLW products described or contained in this document specify the performance, characteristics, and functionality of said products in their standalone state, but do not guarantee the performance, characteristics, and functionality of said products installed in Customer's products or equipment. In order to verify symptoms and conditions that cannot be evaluated in a standalone device, the Customer should ultimately evaluate and test the device installed in the Customer's product device.
- XBLW documentation is only allowed to be copied without any alteration of the content and with the relevant authorization. XBLW assumes no responsibility or liability for altered documents.
- XBLW is committed to becoming the preferred semiconductor brand for customers, and XBLW will strive to provide customers with better performance and better quality products.